

09/03

10/667603

FORM PTO-1449 (Modified)				ATTY. DOCKET NO. FIS920030188US1		SERIAL NO. Unassigned	
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT				APPLICANT: Dureseti Chidambarao, et al.			
(Use several sheets if necessary)				FILING DATE: Concurrently Herewith		GROUP: Unassigned 2829	

REFERENCE DESIGNATION		U.S. PATENT DOCUMENTS				
EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
SBG	6,228,694 B1	5/8/2001	Doyle et al.	—	—	
SBG	6,406,973 B1	6/18/2002	Lee	—	—	
SBG	6,281,532 B1	8/28/2001	Doyle et al.	—	—	
SBG	5,683,934	11/4/97	Candelaria	—	—	
SBG	6,368,931 B1	4/9/2002	Kuhn, et al.	—	—	
SBG	5,310,446	5/10/94	Konishi et al.	—	—	
SBG	4,853,076	8/1/89	Tsaur et al.	—	—	
SBG	US 2002/0090791 A1	7/11/2002	Doyle et al.	—	—	
SBG	US 2002/0074598 A1	6/20/2002	Doyle et al.	—	—	
SBG	6,509,618 B2	7/21/2003	Jan et al.	—	—	
SBG	6,476,462 B2	11/5/2002	Shimizu et al.	—	—	
SBG	6,362,082 B1	3/26/2002	Doyle et al.	—	—	
SBG	6,228,694 B1	5/8/2001	Doyle et al.	—	—	
SBG	5,565,697	10/15/96	Asakawa et al.	—	—	
SBG	US 2003/0040158 A1	2/27/2003	Saitoh	—	—	
SBG	US 2002/0086472 A1	7/4/2002	Roberds et al.	—	—	
SBG	6,521,964 B1	2/18/2003	Jan et al.	—	—	
SBG	6,506,652	01/14/03	Jan, et al.	—	—	

FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
/						YES	NO

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)			
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EXAMINER <i>Ant D. B.</i>	DATE CONSIDERED 10/15/04
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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
SBG	5,081,513	1/14/1992	Jackson, et al.	—	—	
SBG	3,602,841	8/31/1971	McGroddy	—	—	
SBG	6,531,740	3/11/2003	Bosco, et al.	—	—	
SBG	6,531,369	3/11/2003	Ozkan, et al.	—	—	
SBG	6,501,121	12/31/2002	Yu, et al.	—	—	
SBG	6,498,358	12/24/2002	Lach, et al.	—	—	
SBG	6,493,497	12/10/2002	Ramdani, et al.	—	—	
SBG	6,403,975	6/11/2002	Brunner, et al.	—	—	
SBG	6,361,885	3/26/2002	Chou	—	—	
SBG	6,255,169	7/3/2001	Li, et al.	—	—	
SBG	6,246,095	6/12/2001	Brady, et al.	—	—	
SBG	6,165,383	12/26/2000	Chou	—	—	
SBG	6,133,071	10/17/2000	Nagai	—	—	
SBG	6,046,464	4/4/2000	Schetzina	—	—	
SBG	6,025,280	2/15/2000	Brady, et al.	—	—	

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EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)		
SB6		5,940,736	8/17/1999	Brady, et al.	—	—			
SB6		5,880,040	3/9/1999	Sun, et al.	—	—			
SB6		5,861,651	1/19/1999	Brasen, et al.	—	—			
SB6		5,679,965	10/21/1997	Schetzina	—	—			
SB6		5,670,798	9/23/1997	Schetzina	—	—			
SB6		5,561,302	10/1/1996	Candelaria	—	—			
SB6		5,471,948	12/5/1995	Burroughes, et al.	—	—			
SB6		5,459,346	10/17/1995	Asakawa, et al.	—	—			
SB6		5,391,510	2/21/1995	Hsu, et al.	—	—			
SB6		5,371,399	12/6/1994	Burroughes, et al.	—	—			
SB6		5,108,843	4/28/1992	Ohtaka, et al.	—	—			
SB6		5,060,030	10/22/1991	Hoke	—	—			
SB6		4,958,213	9/18/1990	Eklund, et al.	—	—			
SB6		4,665,415	5/12/1987	Esaki, et al.	—	—			

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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

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U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
SBG	5,989,978	11/23/1999	Peidous	—	—	
SBG	6,284,626	9/4/2001	Kim	—	—	
SBG	6,274,444	8/14/2001	Wang	—	—	
SBG	6,261,964	7/17/2001	Wu, et al.	—	—	
SBG	6,221,735	4/24/2001	Manley, et al.	—	—	
SBG	6,117,722	9/12/2000	Wuu, et al.	—	—	
SBG	6,107,143	8/22/2000	Park, et al.	—	—	
SBG	6,090,684	7/18/2000	Ishitsuka, et al.	—	—	
SBG	6,066,545	5/23/2000	Doshi, et al.	—	—	
SBG	6,008,126	12/28/1999	Leedy	—	—	
SBG	5,946,559	8/31/1999	Leedy	—	—	
SBG	5,840,593	11/24/1998	Leedy	—	—	
SBG	5,592,018	1/7/1997	Leedy	—	—	
SBG	5,592,007	1/7/1997	Leedy	—	—	
SBG	5,571,741	11/5/1996	Leedy	—	—	

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EXAMINER <div style="text-align: center; font-size: 1.5em;">SBG</div>	DATE CONSIDERED <div style="text-align: center; font-size: 1.5em;">12/15/04</div>
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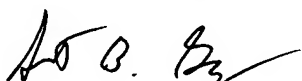
EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
SBG	5,557,122	9/17/1996	Shrivastava, et al.	—	—	
SBG	5,354,695	10/11/1994	Leedy	—	—	
SBG	5,134,085	7/28/1992	Gilgen, et al.	—	—	
SBG	5,006,913	4/9/1991	Sugahara, et al.	—	—	
SBG	4,952,524	8/28/1990	Lee, et al.	—	—	
SBG	4,855,245	8/8/1989	Neppl, et al.	—	—	

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SBG		Kern Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si n-MOSFETs", International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.
SBG		Kern Rim, et al., "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs", 2002 Symposium On VLSI Technology Digest of Technical Papers, IEEE, pp 98-99.
SBG		Gregory Scott, et al., "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress", International Electron Devices Meeting, 34.4.1, IEEE, September 1999.
SBG		F. Ootsuka, et al., "A Highly Dense, High-Performance 130nm node CMOS Technology for Large Scale System-on-a-Chip Application", International Electron Devices Meeting, 23.5.1, IEEE, April 2000.
SBG		Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design", International Electron Devices Meeting, 10.7.1, IEEE, April 2000.
SBG		A. Shimizu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement", International Electron Devices Meeting, IEEE, March 2001.
SBG		K. Ota, et al., "Novel Locally Strained Channel Technique for high Performance 55nm CMOS", International Electron Devices Meeting, 2.2.1, IEEE, February 2002.

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